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AMENDMENTS TO THE CLAIMS:

Claims 1-13 (Canceled)

Claim 14. (Previously presented) A semiconductor light-emitting apparatus of a flip-chip bonding type, comprising:

a transparent base comprising an inorganic material, which has on one side thereof a first bonding pad and a second bonding pad to be connected to a pair of lead frames with a space between the first and the second bonding pads where a semiconductor light-emitting element is fixed, the light-emitting element comprising:

a light-emitting layer;

a substrate disposed between said light emitting layer and said base; and

a positive electrode comprising a light non-transmissible material, said electrode being disposed on an opposite side of said light-emitting layer from said substrate and reflecting light from said light-emitting layer in a direction through said substrate and said base,

wherein said positive electrode is connected by a bonding wire to a surface of one of said first and second bonding pads, one of said pair of lead frames being connected to said surface, and

wherein the inorganic material comprises a fluorescent material dispersed therein.

Claim 15. (Original) A semiconductor light-emitting apparatus of flip chip bonding type as claimed in claim 14, wherein the inorganic material is selected from the group consisting of a SiO₂, sapphire and borosilicate glass.

Claim 16. (Original) A semiconductor light-emitting apparatus of flip chip bonding type as claimed in claim 14, said transparent base is rectangular in its plane view.

Claim 17. (Canceled)

Claim 18. (Previously presented) A semiconductor light-emitting apparatus of flip chip

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bonding type as claimed in claim 14, said transparent base comprising a plurality of layers, and at least one of the layers comprising a fluorescent material.

Claim 19. (Currently amended) A pair of lead frames for use in a light-emitting apparatus of a flip chip bonding type, said apparatus comprising:

a transparent base having a first surface and comprising a fluorescent material;

first and a second bonding pads formed on said first surface; and

a GaN semiconductor light-emitting device fixed on the first surface,

wherein a first lead frame includes a first mount which faces a dominant light emitting direction of the light-emitting apparatus and on which the first bonding pad is to be fixed, and a second lead frame includes a second mount which faces the dominant light emitting direction and on which the second bonding pad is to be fixed,

wherein the light-emitting device comprises a substrate, a light-emitting layer and a positive electrode comprising a light non-transmissible material, said positive electrode being disposed on an opposite side of said light-emitting layer from said substrate and reflecting light from said light-emitting layer in a direction through said substrate and said base,

wherein said positive electrode is connected by a bonding wire to a surface of one of said first and second bonding pads, one of said pair of lead frames being connected to said surface.

Claim 20. (Original) A pair of lead frames according to claim 19, wherein the first lead frame has a first projection on which diffused light from the light-emitting device is to be reflected toward the dominant light-emitting direction, and the second lead frame has a second projection on which diffused light from the light-emitting device is to be reflected toward the dominant light-emitting direction.

Claim 21. (Canceled)

Claim 22. (Previously presented) A semiconductor light-emitting apparatus of flip chip bonding type as claimed in claim 14, wherein the light-emitting layer comprises a multi-quantum well layer.

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Claim 23. (Previously presented) A pair of lead frames for use in a light-emitting apparatus of flip chip bonding type as claimed in claim 19, wherein the light-emitting layer comprises a multi-quantum well layer.

Claims 24-25. (Canceled)

Claim 26. (Currently amended) A semiconductor light-emitting apparatus comprising:
a base;
first and second bonding pads formed on a first surface of said base;
a light-emitting element formed between said first and second pads on said first surface of said base; said light-emitting element comprising:
a substrate;
a light-emitting layer formed on said substrate; and
a first electrode disposed on an opposite side of said light-emitting layer from said base and comprising a light non-transmissible material for reflecting light from said light-emitting layer through said base;
a sealing resin formed on said base and said light-emitting element; and
a fluorescent material which is disposed in said base and is adjacent to said substrate and on an opposite side of said substrate from said light-emitting layer.

Claim 27. (Previously presented) The semiconductor light-emitting apparatus according to claim 26, further comprising:
first and second lead frames electrically connected to said first and second bonding pads, respectively.

Claim 28. (Currently amended) The semiconductor light-emitting apparatus according to claim 27, wherein said ~~light-emitting element further comprises a substrate~~ is disposed between said light-emitting layer and said base, and wherein said first electrode reflects light from said light-emitting layer through said substrate.

Claim 29. (Currently amended) The semiconductor light-emitting apparatus according to

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claim 27, wherein a direction from said light-emitting layer toward said base comprises said a dominant light-emitting direction.

Claim 30. (Previously presented) The semiconductor light-emitting apparatus according to claim 29, wherein said first and second lead frames each comprise a projecting portion which reflects light in said dominant light-emitting direction.

Claim 31. (Previously presented) The semiconductor light-emitting apparatus according to claim 27, wherein said first and second bonding pads are formed on said first surface of said base so as to maximize a distance between said first and second lead frames.

Claim 32. (Previously presented) The semiconductor light-emitting apparatus according to claim 26, wherein first and second bonding pads are formed on opposing outer edges of said first surface of said base.

Claim 33. (Previously presented) The semiconductor light-emitting apparatus according to claim 26, wherein an adhesive adheres said light-emitting element to said first surface of said base.

Claim 34. (Previously presented) The semiconductor light-emitting apparatus according to claim 26, wherein said light-emitting element further comprises a second electrode, said first and second electrodes being connected by bonding wires to said first and second bonding pads, respectively.

Claim 35. (Currently amended) The semiconductor light-emitting apparatus according to claim 34, wherein said first lead frame and one of said bonding wires are connected to a same surface of said first bonding pad, and said second lead frame frames and one of said bonding wires are connected to a same surface of said first and second bonding pad pads.

Claim 36. (Previously presented) The semiconductor light-emitting apparatus according to claim 28, wherein said substrate of said light-emitting element is formed on said base.

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Claim 37. (Canceled)

Claim 38. (Previously presented) The pair of lead frames according to claim 19, wherein said apparatus further comprises a sealing resin formed over said transparent base and said GaN semiconductor light-emitting device.

Claim 39. (Previously presented) A semiconductor light-emitting apparatus comprising:
a transparent base comprising a fluorescent material;
a light-emitting element mounted on the transparent base and having positive and negative electrodes both disposed on one side of the light-emitting element, the positive electrode reflecting light emitted from the light-emitting element;
wires for connecting the positive and negative electrodes to a foreign member; and
a lead frame for holding the transparent base.